

Low frequency transistor

2SA2018 / 2SA2030 / 2SA2119K

The transistor of 500mA class which went only into 2125 size conventionally was attained in 1608 sizes or 1208 sizes.

●Applications

For switching, for muting.

●Features

- 1) A collector current is large.
- 2) Collector saturation voltage is low.

$$V_{CE(sat)} \leq 250\text{mA}$$

$$\text{At } I_C = 200\text{mA} / I_B = 10\text{mA}$$

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	V_{CBO}	15	V	
Collector-emitter voltage	V_{CEO}	12	V	
Collector current	I_C	500	mA	
	I_{CP}	1	A *	
Collector power dissipation	P_C	VMT3	150	mW
		EMT3		
		SMT3		
Junction temperature	T_j	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	

*Single pulse, Pw=1ms

●External dimensions (Unit : mm)

2SA2018

ROHM : EMT3 Abbreviated symbol : BW (1) Emitter
 EIAJ : SC-75A (2) Base
 JEDEC : SOT-416 (3) Collector

2SA2030

ROHM : VMT3 Abbreviated symbol : BW (1) Base
 (2) Emitter
 (3) Collector

2SA2119K

ROHM : SMT3 Abbreviated symbol : BW (1) Emitter
 EIAJ : SC-59 (2) Base
 JEDEC : SOT-346 (3) Collector

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	15	-	-	V	$I_C=10\mu\text{A}$
Collector-emitter breakdown voltage	BV_{CEO}	12	-	-	V	$I_C=1\text{mA}$
Emitter-base breakdown voltage	BV_{EBO}	6	-	-	V	$I_E=10\mu\text{A}$
Collector cutoff current	I_{CBO}	-	-	100	nA	$V_{CB}=15\text{V}$
DC current transfer ratio	h_{FE}	270	-	680	-	$V_{CE}=2\text{V} / I_C=10\text{mA}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	100	250	mV	$I_C=200\text{mA} / I_B=10\text{mA}$
Transition frequency	f_T	-	260	-	MHz	$V_{CE}=2\text{V}, I_E=10\text{mA}, f_T=100\text{MHz}$
Output capacitance	C_{ob}	-	6.5	-	pF	$V_{CB}=10\text{V}, I_E=0\text{A}, f=1\text{MHz}$

Transistors

●Packaging specifications and hFE

Type	hFE	Package name	Taping		
		Code	T146	TL	T2L
		Basic ordering unit (pieces)	3000	3000	8000
2SA2119K			○	—	—
2SA2018			—	○	—
2SA2030			—	—	○

●Electrical characteristic curves

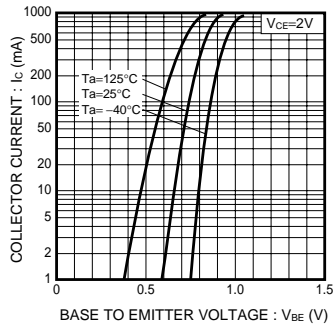


Fig.1 Grounded Emitter Propagation Characteristics

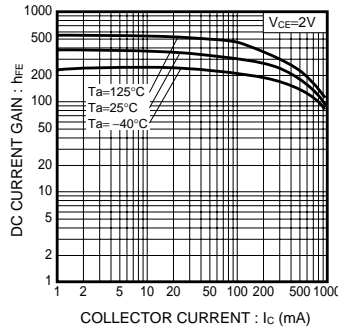


Fig.2 DC Current Gain vs. Collector Current

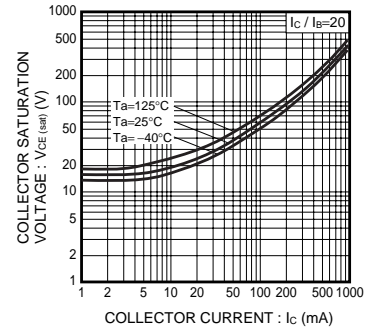


Fig.3 Collector-Emitter Saturation Voltage vs. Collector Current (I)

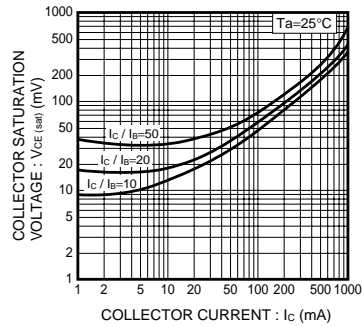


Fig.4 Collector-Emitter Saturation Voltage vs. Collector Current (II)

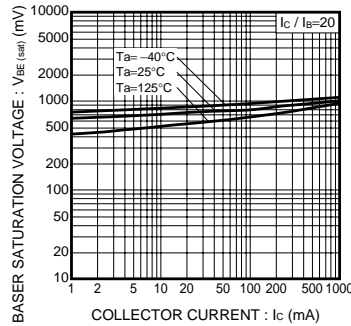


Fig.5 Base-Emitter Saturation Voltage vs. Collector Current

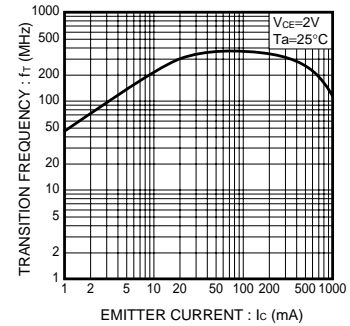


Fig.6 Gain Bandwidth Product vs. Emitter Current

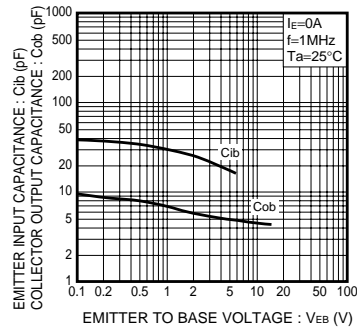


Fig.7 Collector Output Capacitance vs. Collector-Base Voltage
Emitter Input Capacitance vs. Emitter-Base Voltage

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